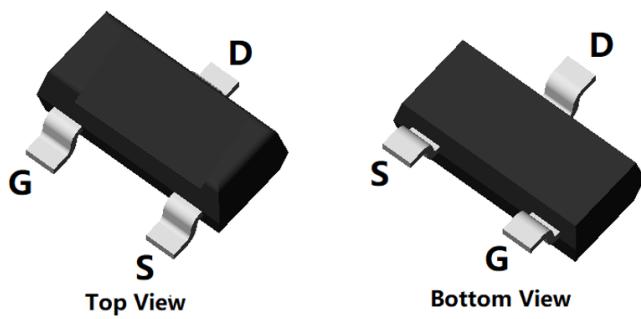
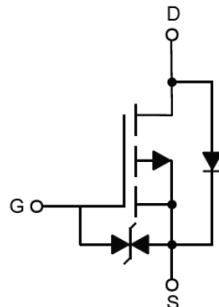


P-Channel Enhancement Mode Field Effect Transistor



SOT-23



Product Summary

- V_{DS} -20 V
- I_D -5 A
- $R_{DS(on)}$ (at $V_{GS}=-4.5V$) <40 mΩ
- $R_{DS(on)}$ (at $V_{GS}=-2.5V$) <70 mΩ
- ESD Protected Up to 2.0KV (HBM)

General Description

- Split gate trench MOSFET technology
- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power management
- Portable equipment

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	-20	V
Gate-source Voltage		V_{GS}	± 10	V
Drain Current	$T_A=25^\circ C$	I_D	-5	A
	$T_A=100^\circ C$		-3.2	
Pulsed Drain Current ^A		I_{DM}	-30	A
Total Power Dissipation ^C	$T_A=25^\circ C$	P_D	1	W
	$T_A=100^\circ C$		0.4	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 ~ +150	°C

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	Steady-State	$R_{\theta JA}$	100	120	°C/W

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
ZXL3415KC	F2	3415C	3000	30000	120000	7" reel

ZXL3415KC

■ Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-20\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	μA
		$V_{\text{DS}}=-20\text{V}, V_{\text{GS}}=0\text{V}, T_J=150^\circ\text{C}$	-	-	-100	
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 10\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 10	
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-0.55	-0.85	-1.25	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-5\text{A}$	-	28	40	$\text{m}\Omega$
		$V_{\text{GS}}=-2.5\text{V}, I_{\text{D}}=-4\text{A}$	-	50	70	
Diode Forward Voltage	V_{SD}	$I_{\text{S}}=-5\text{A}, V_{\text{GS}}=0\text{V}$	-	-0.9	-1.2	V
Gate resistance	R_{G}	f=1MHz, Open drain	-	16	-	Ω
Maximum Body-Diode Continuous Current	I_{S}		-	-	-5	A
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{\text{DS}}=-10\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$	-	540	-	pF
Output Capacitance	C_{oss}		-	120	-	
Reverse Transfer Capacitance	C_{rss}		-	100	-	
Switching Parameters						
Total Gate Charge	Q_{g}	$V_{\text{GS}}=-10\text{V}, V_{\text{DS}}=-10\text{V}, I_{\text{D}}=-5\text{A}$	-	13	-	nC
Gate-Source Charge	Q_{gs}		-	2	-	
Gate-Drain Charge	Q_{gd}		-	2	-	
Reverse Recovery Charge	Q_{rr}	$I_{\text{F}}=-5\text{A}, \text{di}/\text{dt}=100\text{A}/\text{us}$	-	2.5	-	nC
Reverse Recovery Time	t_{rr}		-	20	-	ns
Turn-on Delay Time	$t_{\text{D}(\text{on})}$	$V_{\text{GS}}=-10\text{V}, V_{\text{DD}}=-10\text{V}, I_{\text{D}}=-5\text{A}$ $R_{\text{GEN}}=2.2\Omega$	-	5	-	ns
Turn-on Rise Time	t_{r}		-	47	-	
Turn-off Delay Time	$t_{\text{D}(\text{off})}$		-	52	-	
Turn-off fall Time	t_{f}		-	69	-	

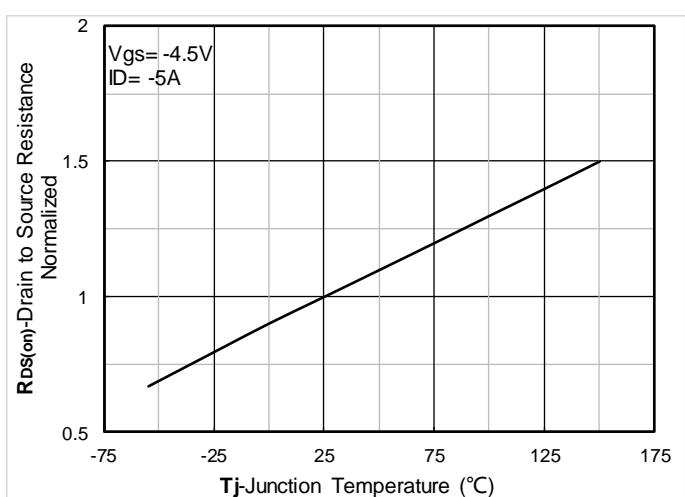
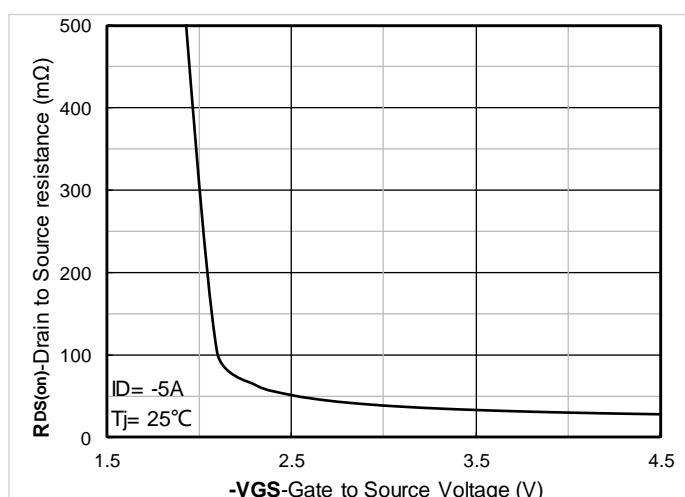
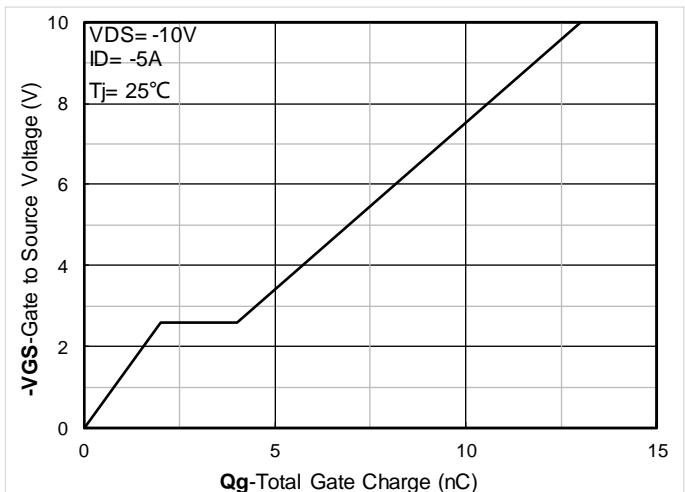
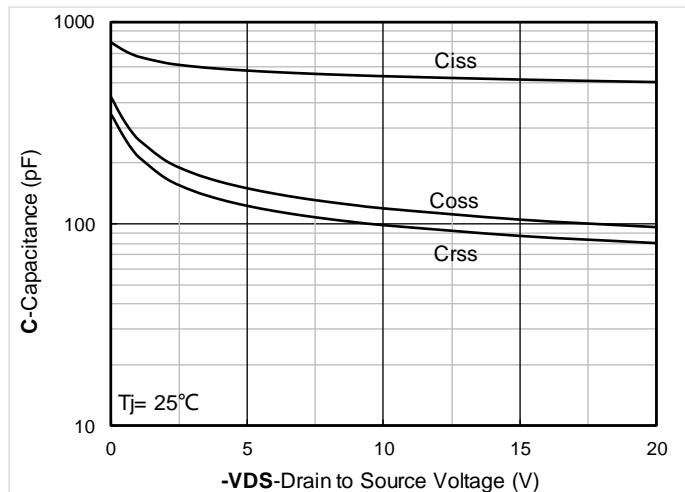
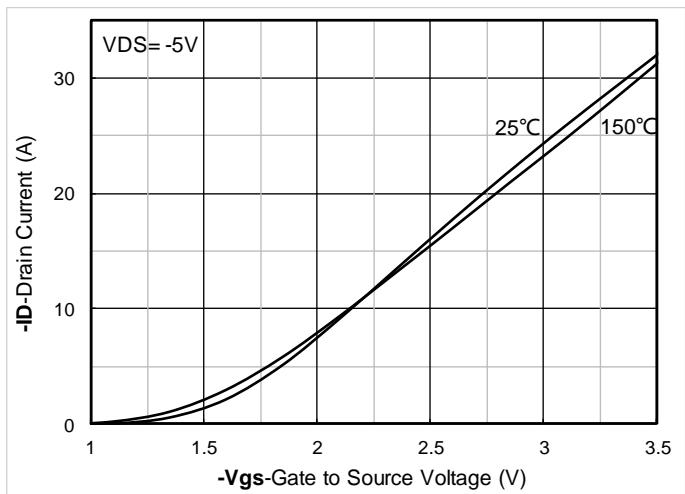
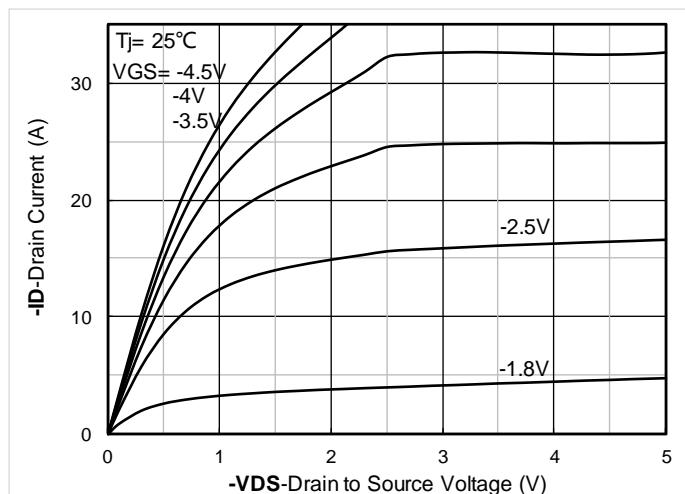
A. Repetitive rating; pulse width limited by max. junction temperature.

B. P_d is based on max. junction temperature, using junction-case and junction-ambient thermal resistance.

C. The value of R_{GJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in the still air environment with $T_A=25^\circ\text{C}$.

The maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design.

■ Typical Electrical and Thermal Characteristics Diagrams



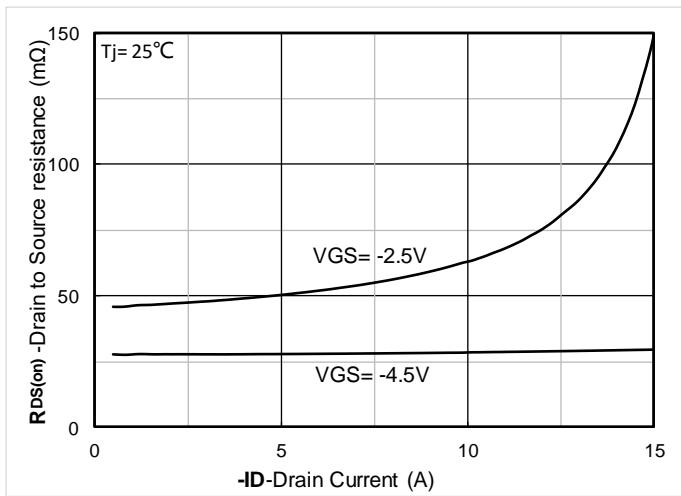


Figure 7. $R_{DS(on)}$ VS Drain Current

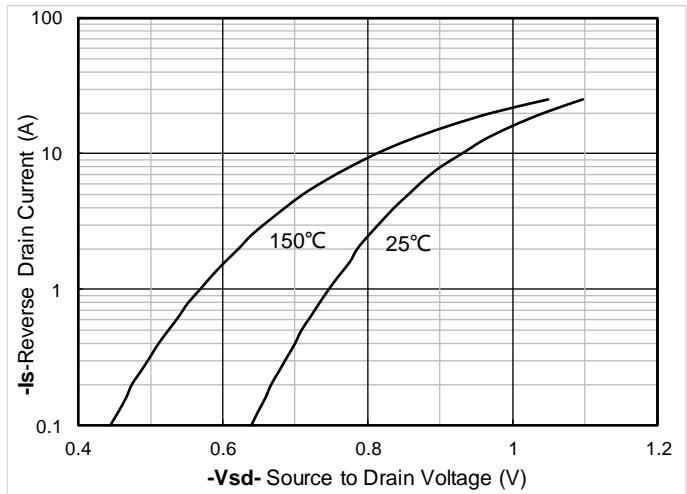


Figure 8. Forward characteristics of reverse diode

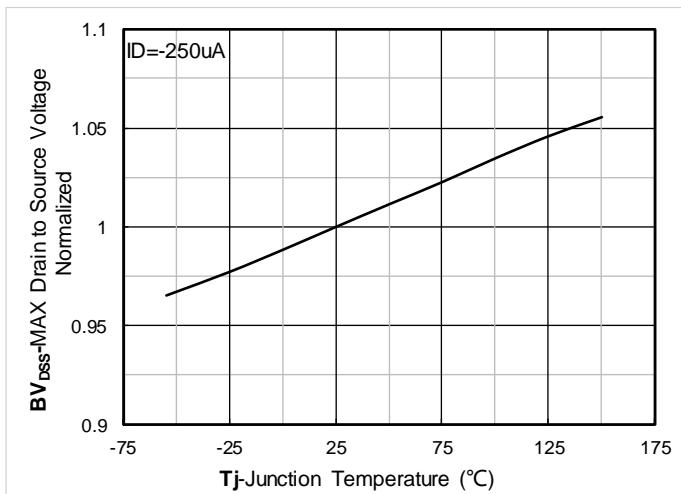


Figure 9. Normalized breakdown voltage

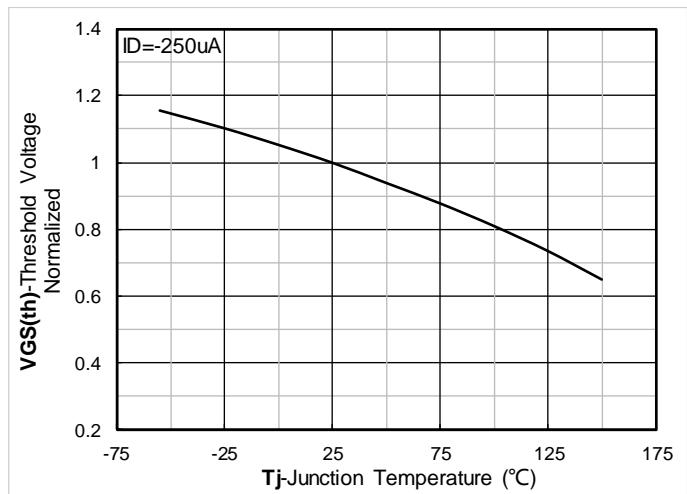


Figure 10. Normalized Threshold voltage

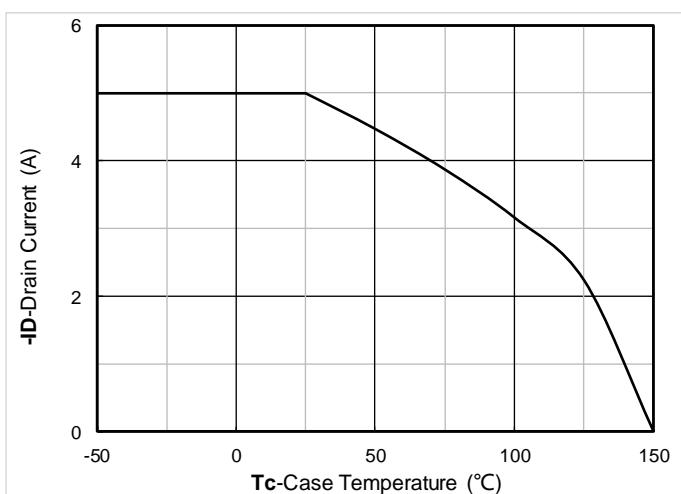


Figure 11. Current dissipation

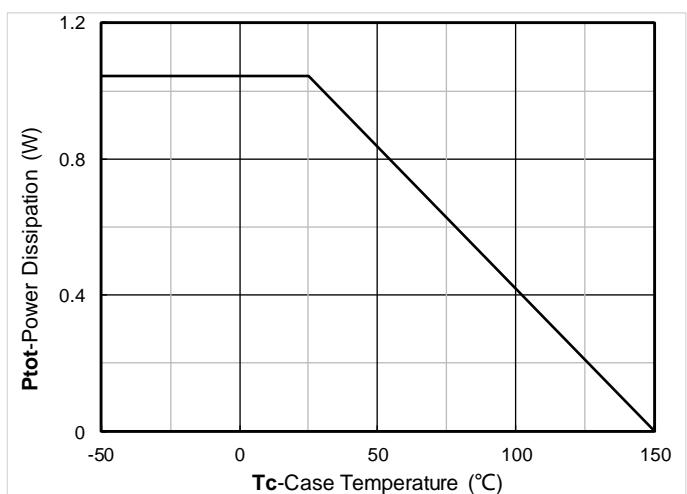


Figure 12. Power dissipation

ZXL3415KC

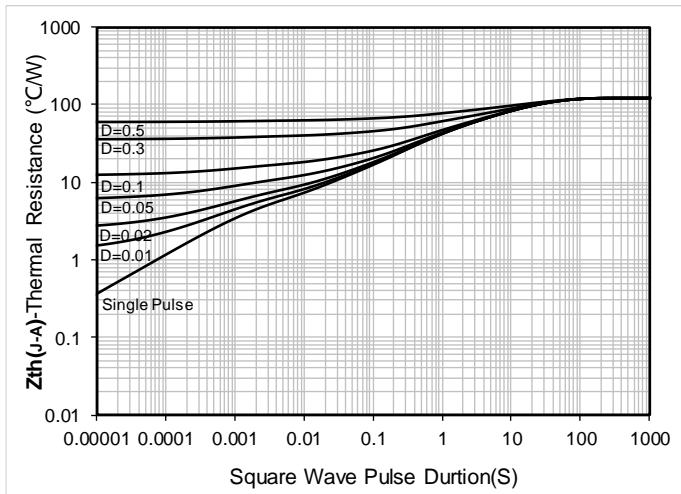


Figure 13. Maximum Transient Thermal Impedance

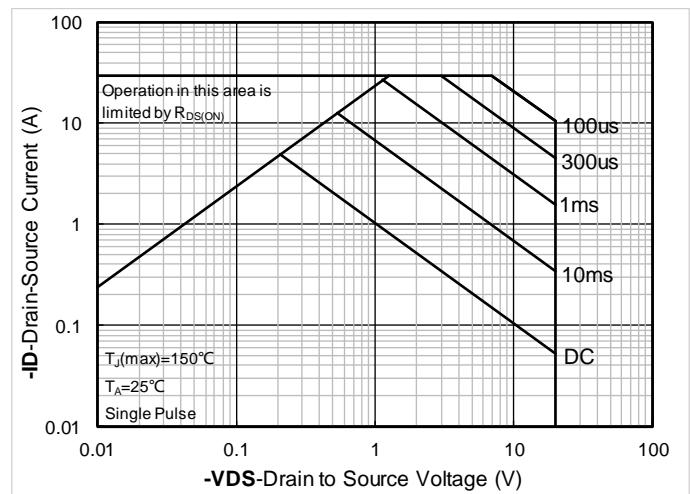
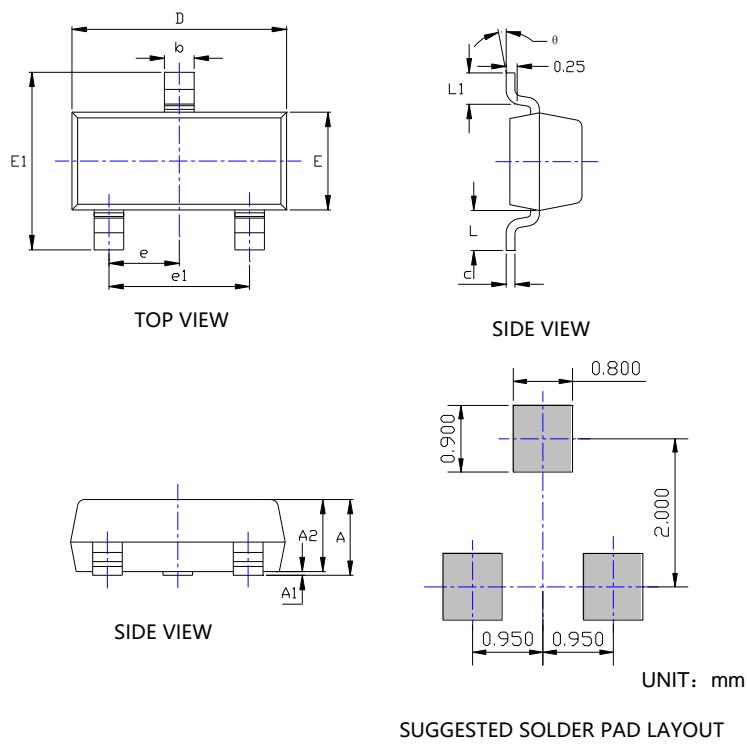


Figure 14. Safe Operation Area

ZXL3415KC

■ SOT-23 Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.035	0.045	0.900	1.150
A1	0.000	0.004	0.000	0.100
A2	0.035	0.041	0.900	1.050
b	0.012	0.020	0.300	0.500
c	0.004	0.008	0.100	0.200
D	0.110	0.118	2.800	3.000
E	0.047	0.055	1.200	1.400
E1	0.089	0.100	2.250	2.550
e	0.037TYP		0.950TYP	
e1	0.071	0.079	1.800	2.000
L	0.022REF		0.550REF	
L1	0.012	0.020	0.300	0.500
θ	0°	8°	0°	8°

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.